Abstracts

Silicon carbide MESFETs performances and application in broadcast power amplifiers

F. Temcamani, P. Pouvil, O. Noblanc, C. Brylinski, P. Bannelier, B. Darges and J.P. Prigent. "Silicon carbide MESFETs performances and application in broadcast power amplifiers." 2001 MTT-S International Microwave Symposium Digest 01.2 (2001 Vol. II [MWSYM]): 641-644 vol.2.

We present DC, small signal and power characterization of recent Thomson silicon carbide MESFETs. We present also performances of SiC power amplifiers designed for use in broadcast digital television. A comparison with a LDMOS amplifier showed that SiC is a very promising material for microwave and RF power amplification.

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